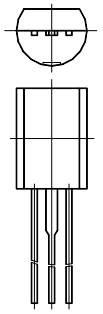
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92L Plastic-Encapsulate Transistors

2SB892 TRANSISTOR (PNP)

TO-92L

1. EMITTER
2. COLLECTOR
3. BASE



123

FEATURE

- Power supplies, relay drivers, lamp drivers, and automotive wiring
- Low saturation voltage.
- Large current capacity and wide ASO.

MAXIMUM RATINGS (T_A=25℃ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current -Continuous	-2	A
P_C	Collector Dissipation	0.75	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55-150	℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	I_C= -100μA , I_E=0	-60		V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	I_C= -1mA , I_B=0	-50		V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	I_E=- 100μA, I_C=0	-6		V
Collector cut-off current	I_{CBO}	V_{CB}= -50V , I_E=0		-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= -4V , I_C=0		-0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=-2V, I_C= -100mA	100	560	
	$h_{FE(2)}$	V_{CE}=-2V, I_C= -1.5A	40		
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C= -1A, I_B= -50mA		-0.4	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C= -1A, I_B= -50mA		-1.2	V
Transition frequency	f_T	V_{CE}= -10 V, I_C= -50mA	150		MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	R	S	T	U
Range	100-200	140-280	200-400	280-560

Typical characteristics

2SB892